

Description

The FDN308P uses advanced trench technology to provide excellent $R_{DS(ON)}$, This device is suitable for use as a load switch or in PWM applications.

General Features

 $V_{DS} = -20V, I_D = -3A$ $R_{DS(ON)} < 80m\Omega @ V_{GS} = -4.5V$

Application

Battery protection

Load switch

Uninterruptible power supply

Package Marking and Ordering Information

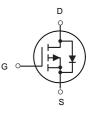
Product ID	Pack	Brand	Qty(PCS)
FDN308P	SOT-23	HXY MOSFET	3000

Absolute Maximum Ratings (TA=25°C unless otherwise noted)

Symbol	Symbol Parameter		Unit	
VDS	Drain-Source Voltage	-20	V	
Vgs	Gate-Source Voltage	±12	V	
ID	Drain Current-Continuous	-3	A	
Ідм	Drain Current-Pulsed (Note 1)	-10	A	
PD	Maximum Power Dissipation	1	W	
Tj,Tstg	Operating Junction and Storage Temperature Range	-55 To 150	°C	
Reja	Thermal Resistance, Junction-to-Ambient (Note 2)	125	°C/W	



SOT-23



P-Channel MOSFET



Electrical Characteristics (T_A=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics				I		I
Drain-Source Breakdown Voltage	BV _{DSS}	V_{GS} =0V I _D =-250µA	-20	-24	-	V
Zero Gate Voltage Drain Current	ldss	V_{DS} =-20V, V_{GS} =0V	-	-	-1	μA
Parameter	Symbol	Condition	Min	Тур	Мах	Unit
Gate-Body Leakage Current	Igss	V_{GS} =±12V, V_{DS} =0V	-	-	±100	nA
On Characteristics (Note 3)			-11	I		L
Gate Threshold Voltage	VGS(th)	$V_{DS}=V_{GS}$, $I_D=-250\mu A$	-0.4	-0.7	-1	V
		V_{GS} =-4.5V, I _D =-3A	-	60	80	mΩ
Drain-Source On-State Resistance	Rds(on)	V_{GS} =-2.5V, I _D =-2A	-	85	103	mΩ
Forward Transconductance	g fs	V _{DS} =-5V,I _D =-2A	5	-	-	S
Dynamic Characteristics (Note4)				I		I
Input Capacitance	Clss		-	405	-	PF
Output Capacitance	Coss	V_{DS} =-10V, V_{GS} =0V,	-	75	-	PF
Reverse Transfer Capacitance	Crss	F=1.0MHz	-	55	-	PF
Switching Characteristics (Note 4)			-11	I		L
Turn-on Delay Time	td(on)		-	11	-	nS
Turn-on Rise Time	tr	V _{DD} =-10V,I _D =-1A V _{GS} =-	-	35	-	nS
Turn-Off Delay Time	td(off)	4.5V,R _{GEN} =10Ω	-	30	-	nS
Turn-Off Fall Time	tr		-	10	-	nS
Total Gate Charge	Qg		-	3.3	12	nC
Gate-Source Charge	Qgs	V _{DS} =-10V, I _D =-3A,	-	0.7	-	nC
Gate-Drain Charge	Qgd	V _{GS} =-2.5V	-	1.3	-	nC
Drain-Source Diode Characteristics				<u>I</u>		<u>I</u>
Diode Forward Voltage (Note 3)	Vsd	V _{GS} =0V, I _S =1.3A	-	-	-1.2	V
Diode Forward Current (Note 2)	ls		-	-	-3	Α

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.

2. Surface Mounted on FR4 Board, $t \le 10$ sec.

3. Pulse Test: Pulse Width \leq 300µs, Duty Cycle \leq 2%.

4. Guaranteed by design, not subject to production



Typical Electrical and Thermal Characteristics

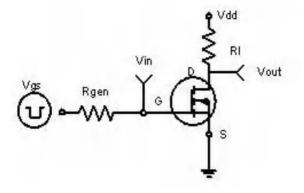
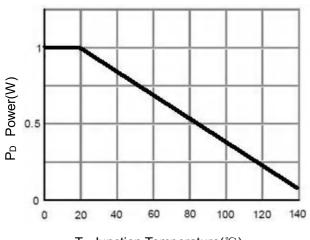
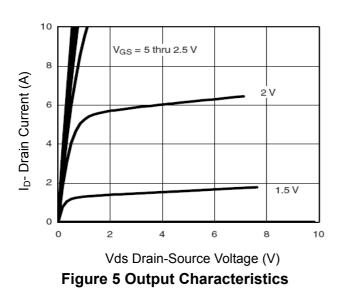


Figure 1:Switching Test Circuit



T_J-Junction Temperature(℃) Figure 3 Power Dissipation



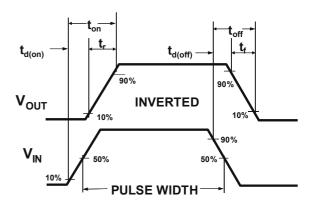
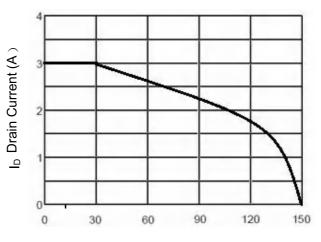


Figure 2:Switching Waveforms



TJ-Junction Temperature(℃) Figure 4 Drain Current

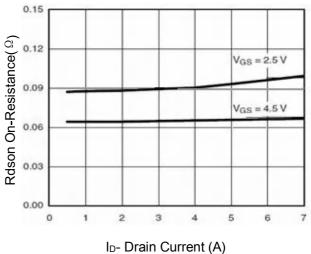
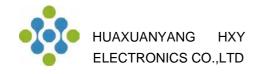
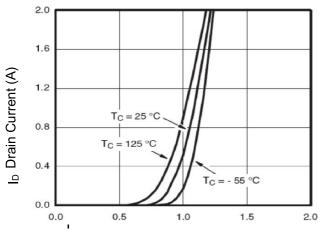


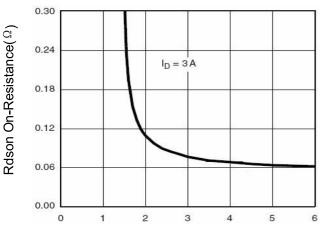
Figure 6 Drain-Source On-Resistance



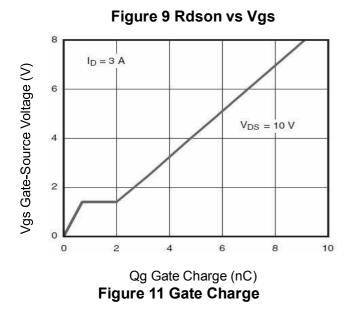


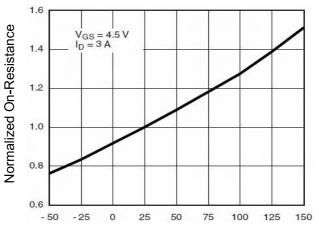
Vgs Gate-Source Voltage (V)



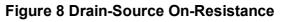


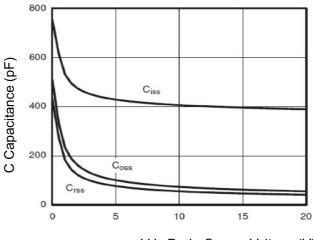
Vgs Gate-Source Voltage (V)





T_J-Junction Temperature(°C)





Vds Drain-Source Voltage (V)



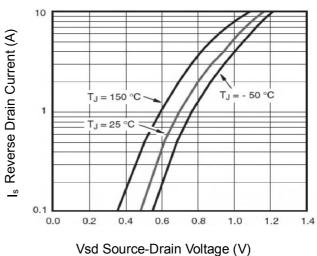
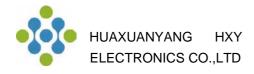


Figure 12 Source- Drain Diode Forward

Figure 7 Transfer Characteristics



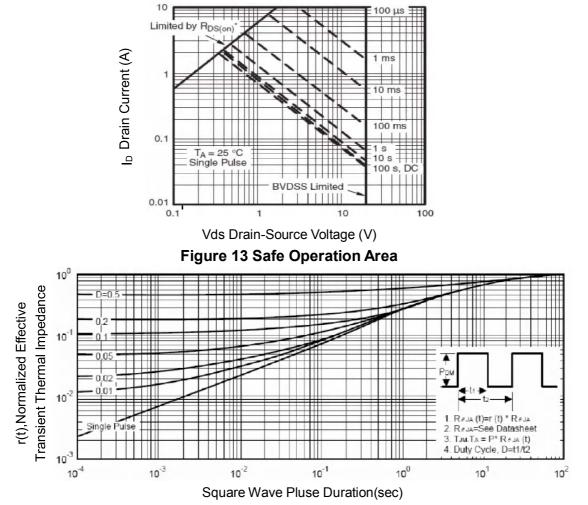
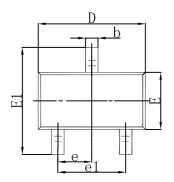
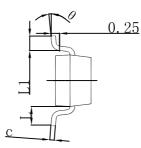


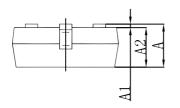
Figure 14 Normalized Maximum Transient Thermal Impedance



SOT-23 Package Outline Dimensions

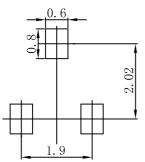






Symbol	Dimensions In Millimeters		Dimensions In Inches		
	Min	Max	Min	Max	
Α	0.900	1.150	0.035	0.045	
A1	0.000	0.100	0.000	0.004	
A2	0.900	1.050	0.035	0.041	
b	0.300	0.500	0.012	0.020	
С	0.080	0.150	0.003	0.006	
D	2.800	3.000	0.110	0.118	
Е	1.200	1.400	0.047	0.055	
E1	2.250	2.550	0.089	0.100	
e	0.950 TYP		0.037 TYP		
e1	1.800	2.000	0.071	0.079	
L	0.550 REF		0.022 REF		
L1	0.300	0.500	0.012	0.020	
θ	0°	8°	0°	8°	

SOT-23 Suggested Pad Layout



Note: 1.Controlling dimension:in millimeters.

2.General tolerance:± 0.05mm.
 3.The pad layout is for reference purposes only.



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